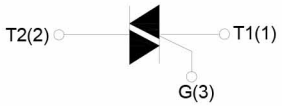
DESCRIPTION:

With high ability to withstand the shock loading of large current, **VSA06/VSB06** triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, the products especially recommended for use on inductive load.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM} /V_{RRM}	600/800	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	℃
Operating junction temperature range		T_j	-40 - 125	℃
Repetitive peak off-state voltage (T_j=25℃)		V_{DRM}	600/800	V
Repetitive peak reverse voltage (T_j=25℃)		V_{RRM}	600/800	V
RMS on-state current	TO-220A(Ins)/ TO-220F(Ins)/ TO-251 (T_C=100℃)	$I_{T(RMS)}$	6	A
	TO-220B(Non-Ins) (T_C=105 ℃)			
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	60	A
I^2t value for fusing (tp=10ms)		I^2t	18	A^2s
Critical rate of rise of on-state current (I_G=2×I_{GT})	I - II -III	dI/dt	50	A/μs
	IV		10	

Peak gate current	I_{GM}	2	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value		Unit
				C	B	
I_{GT}	V_D =12V R_L =30Ω	Ⅰ-Ⅱ-Ⅲ	MAX	25	50	mA
		Ⅳ		50	70	
V_{GT}		ALL	MAX	1.5		V
V_{GD}	V_D =V_{DRM} T_j =125℃ R_L =3.3KΩ	ALL	MIN	0.2		V
I_L	I_G =1.2I_{GT}	Ⅰ-Ⅲ-Ⅳ	MAX	50	70	mA
		Ⅱ		60	80	
I_H	I_{TM} =0.2A		MAX	40	60	mA
dV/dt	V_D=2/3V_{DRM} Gate Open T_j =125℃		MIN	200	500	V/μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	I_{TM} =8.5A tp=380μs	T_j=25℃	1.5	V
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25℃	5	μA
I_{RRM}		T_j=125℃	1	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins) TO-220F(Ins)	2.9	℃/W
		TO-220B(Non-Ins)	2.3	
		TO-251	2.7	

FIG.1: Maximum power dissipation versus RMS on-state current

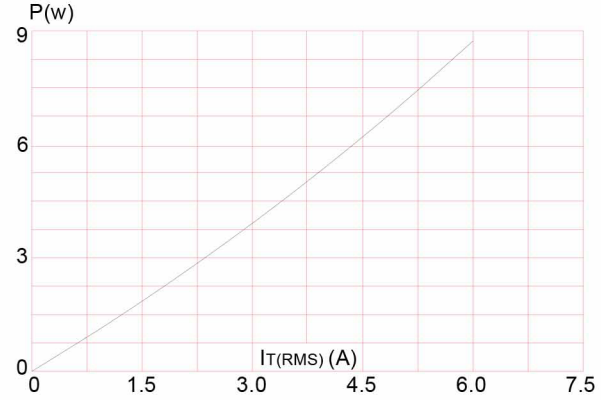


FIG.2: RMS on-state current versus case temperature

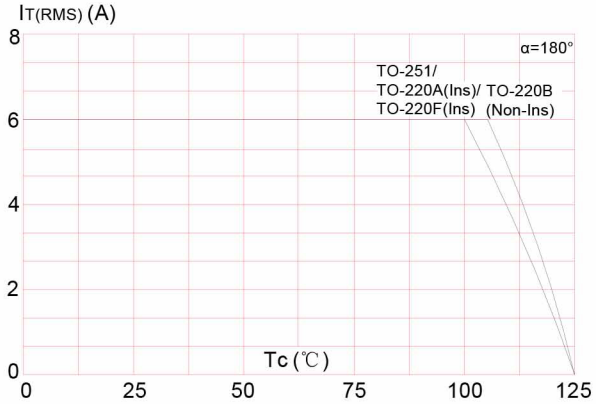


FIG.3: Surge peak on-state current versus number of cycles

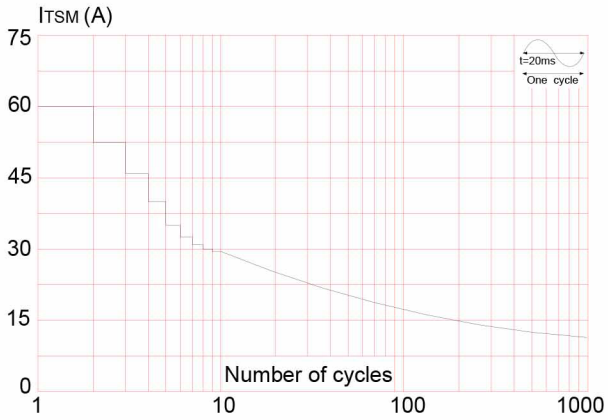


FIG.4: On-state characteristics (maximum values)

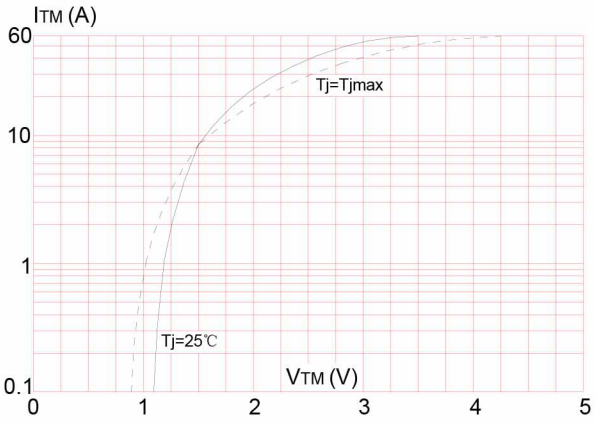


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I^2t (Ⅰ-Ⅱ-Ⅲ:dI/dt < 50A/μs; Ⅳ:dI/dt < 10A/μs)

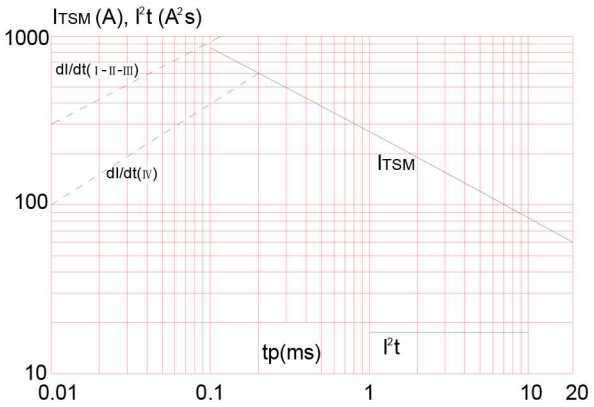


FIG.6: Relative variations of gate trigger current versus junction temperature

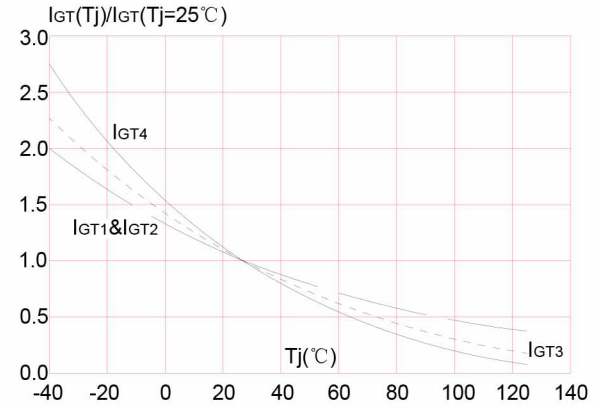


FIG.7: Relative variations of holding current versus junction temperature

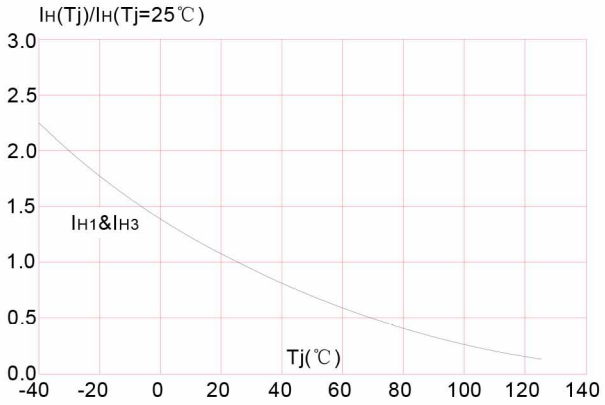


FIG.8: Relative variations of latching current versus junction temperature